EPISTAR

AlGaInP PN-series LED Chip

> Mechanical Specification:

- (1) Dimension
 - Chip size: 42 mil x 42 mil (1076±25 μm x 1076±25 μm)
 - Thickness: 8.8 mil (225±25 μm)
 - N bonding pad: 4.7 mil (120 \pm 10 μ m)

(2) Metallization

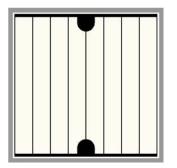
- Topside N electrode (x2): Au alloy
- Backside P electrode: Au alloy

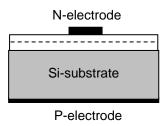
Features:

- \cdot High radiant flux
- \cdot Thin film structure
- · Vertical electrode
- · High driving current

Applications:

- Horticulture lighting
- · Medical appliances





> Electro-optical Characteristics at 25°C:

Parameter	Symbol		Condition	Min.	Тур.	Max.	Unit
Forward Voltage	Vf1		lf = 10μΑ	1.3	-	-	V
	Vf2		lf = 350mA	-	2.1	2.2	V
Reverse Current	Ir		Vr = 10V	-	-	5.0	μΑ
Peak Wavelength ⁽¹⁾	λр		lf = 350mA	650	660	670	nm
Spectra Half-width	Δλ		lf = 350mA	-	16	-	nm
Radiant flux ⁽²⁾⁽³⁾	Ро	H15	If = 350mA	360	-	-	mW
		H16		400	-	-	

Note:

(1) Basically, the wavelength span is 20nm; however, customers' special requirements are also welcome.

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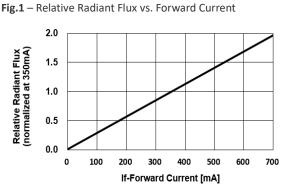
(3) Radiant flux is measured by $\ensuremath{\mathsf{EPISTAR's}}$ equipment on bare chips.

Parameter	Symbol	Condition	Rating	Unit
Forward DC Current	If	Ta = 25°C	≤ 700	mA
Reverse Voltage	Vr	Ta = 25°C	≤ 10	V
Junction Temperature	Тј	-	≤ 115	°C
Storage Temperature	Tstg	Chip	-40 ~ +85	°C
		Chip-on-tape/storage	5 ~ 35	°C
		Chip-on-tape/transportation	-20 ~ +65	°C
Temperature during Packaging	-	- 280(<10sec)		°C

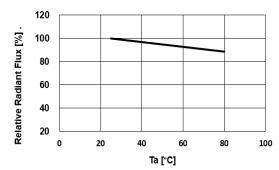
> Absolute Maximum Ratings:

Note: Maximum ratings are package dependent. The above maximum ratings were determined using a Metal Core Printed Circuit Board (MCPCB) without an encapsulant. Stresses in excess of the absolute maximum ratings such as forward current and junction temperature may cause damage to the LED.

> Characteristic Curves:









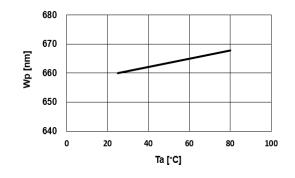


Fig.2 – Forward Current vs. Forward Voltage

